

#### 20V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT23

## **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(on)</sub>            | I <sub>D</sub> Max (Note 5)   |
|----------------------|--------------------------------|-------------------------------|
| 20V                  | 175mΩ @ V <sub>GS</sub> = 4.5V | 1.40A @ T <sub>A</sub> = 25°C |
|                      | 240mΩ @ V <sub>GS</sub> = 2.5V | 1.20A @ T <sub>A</sub> = 25°C |
|                      | 360mΩ @ V <sub>GS</sub> = 1.8V | 1.0A @ T <sub>A</sub> = 25°C  |

# **Features and Benefits**

- On resistance <200mΩ</li>
- Low Gate Threshold Voltage
- Fast Switching Speed
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- ESD Protected Gate 2kV
- Qualified to AEC-Q101 Standards for High Reliability

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load switch

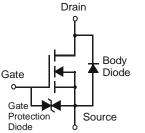
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin
- Weight: 0.08 grams (approximate)

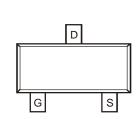




Top View







Top View

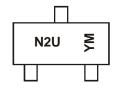
## Ordering Information (Note 3)

| Part Number | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|-------------|---------|--------------------|-----------------|-------------------|
| DMN2300U-7  | N2U     | 7                  | 8               | 3000              |

Notes:

- 1. No purposefully added lead
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**

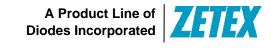


N2U = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

## Date Code Key

| Year  | 201 | 1   | 2012 |     | 2013 | 20  | 14  | 2015 |     | 2016 | 2   | 2017 |
|-------|-----|-----|------|-----|------|-----|-----|------|-----|------|-----|------|
| Code  | Υ   |     | Z    |     | Α    | [   | 3   | С    |     | D    |     | Е    |
| Month | Jan | Feb | Mar  | Apr | May  | Jun | Jul | Aug  | Sep | Oct  | Nov | Dec  |
| Code  | 1   | 2   | 3    | 4   | 5    | 6   | 7   | 8    | 9   | 0    | N   | D    |





# **Maximum Ratings** @ $T_A = 25$ °C unless otherwise specified

| Characteristic                |                                       |                 | Symbol           | Value                | Unit |
|-------------------------------|---------------------------------------|-----------------|------------------|----------------------|------|
| Drain-Source Voltage          |                                       |                 | V <sub>DSS</sub> | 20                   | V    |
| Gate-Source Voltage           |                                       |                 | V <sub>GSS</sub> | ±8                   | V    |
| Continuous Drain Current      | Steady T <sub>A</sub> = 25°C (Note 5) |                 | I <sub>D</sub>   | 1.40<br>1.01<br>1.24 | А    |
| Pulsed Drain Current (Note 6) |                                       | I <sub>DM</sub> | 11               | Α                    |      |

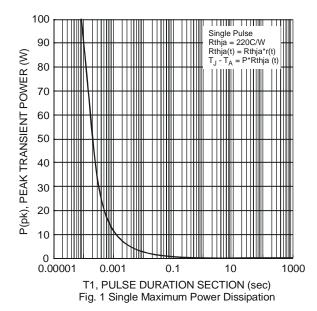
## Thermal Characteristics @TA = 25°C unless otherwise specified

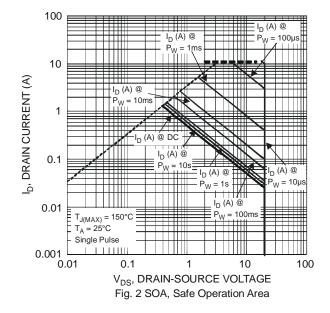
| Characteristic                          | Symbol            | Value            | Unit                |      |
|---|-------------------|------------------|---------------------|------|
| Power Dissipation                       | (Note 4)          | Б                | 0.43                | W    |
| Power Dissipation                       | (Note 5)          | PD               | P <sub>D</sub> 0.55 |      |
| Thermal Decistores, Junction to Ambient | (Note 4)          |                  | 288                 | °C/W |
| Thermal Resistance, Junction to Ambient | (Note 5)          | R <sub>0JA</sub> | 228                 | °C/W |
| Operating and Storage Temperature Range | $T_J$ , $T_{STG}$ | -55 to +150      | °C                  |      |

Notes:

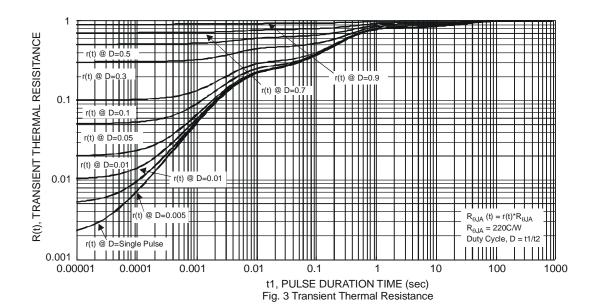
- 4. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
- 5. Device mounted on 25mm X 25mm square copper plate with FR-4 substrate PC board, 2oz copper
- 6. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.

## **Thermal Characteristics**







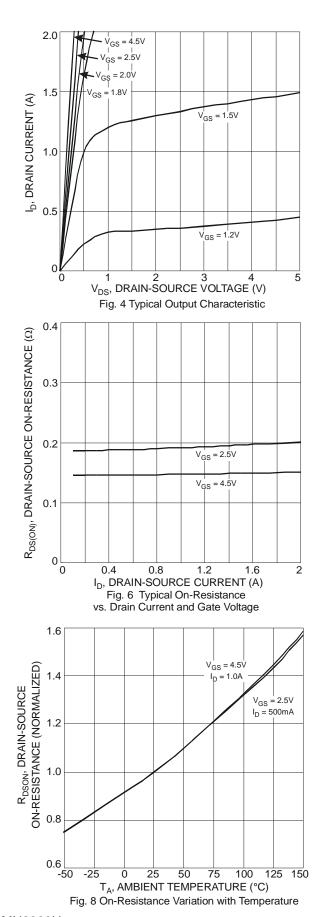


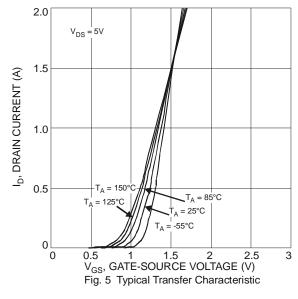
Electrical Characteristics @TA = 25°C unless otherwise specified

| Characteristic  | Symbol               | Min  | Тур  | Max  | Unit | Test Condition                               |  |
|---|----------------------|------|------|------|------|--|--|
| OFF CHARACTERISTICS (Note 7)                          |                      |      |      |      |      |  |  |
| Drain-Source Breakdown Voltage                        | BV <sub>DSS</sub>    | 20   | -    | -    | V    | $V_{GS} = 0V, I_{D} = 10\mu A$               |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C | I <sub>DSS</sub>     | -    | -    | 1    | μΑ   | $V_{DS} = 20V, V_{GS} = 0V$                  |  |
| Gate-Source Leakage                                   | I <sub>GSS</sub>     | -    | -    | 10   | μΑ   | $V_{GS} = \pm 8V$ , $V_{DS} = 0V$            |  |
| ON CHARACTERISTICS (Note 7)                           |                      |      |      |      |      | _  |  |
| Gate Threshold Voltage                                | $V_{GS(th)}$         | 0.45 | -    | 0.95 | V    | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$         |  |
|   |                      |      |      | 175  |      | $V_{GS} = 4.5V, I_D = 300mA$                 |  |
| Static Drain-Source On-Resistance                     | R <sub>DS (ON)</sub> | -    |      | 240  | mΩ   | $V_{GS} = 2.5V, I_D = 250mA$                 |  |
|   | , ,                  |      |      | 360  |      | $V_{GS} = 1.8V, I_D = 100mA$                 |  |
| Forward Transfer Admittance                           | Y <sub>fs</sub>      | 40   | -    | -    | mS   | $V_{DS} = 3V$ , $I_D = 30mA$                 |  |
| Diode Forward Voltage                                 | V <sub>SD</sub>      | -    | 0.7  | 1.2  | V    | $V_{GS} = 0V, I_S = 300mA$                   |  |
| DYNAMIC CHARACTERISTICS (Note 7)                      |                      |      |      | -    |      |  |  |
| Input Capacitance                                     | C <sub>iss</sub>     | -    | 64.3 | -    | pF   | ), OF), ), O),                               |  |
| Output Capacitance                                    | Coss                 | -    | 6.1  | -    | pF   | $V_{DS} = 25V, V_{GS} = 0V,$<br>- f = 1.0MHz |  |
| Reverse Transfer Capacitance                          | C <sub>rss</sub>     | -    | 4.5  | -    | pF   | 1 = 1.000112                                 |  |
| Gate Resistance                                       | Rg                   | -    | 70   | -    | Ω    | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$   |  |
| Total Gate Charge                                     | Qq                   | -    | 1.6  | -    | nC   | 451414                                       |  |
| Gate-Source Charge                                    | Q <sub>qs</sub>      | -    | 0.2  | -    | nC   | $V_{GS} = 4.5V, V_{DS} = 15V,$               |  |
| Gate-Drain Charge                                     | $Q_{qd}$             | -    | 0.2  | -    | nC   | - I <sub>D</sub> = 1A                        |  |
| Turn-On Delay Time                                    | t <sub>D(on)</sub>   | -    | 3.5  | -    | ns   |  |  |
| Turn-On Rise Time                                     | t <sub>r</sub>       | -    | 2.8  | -    | ns   | $V_{DS} = 10V, I_{D} = 1A$                   |  |
| Turn-Off Delay Time                                   | t <sub>D(off)</sub>  | -    | 38   | -    | ns   | $V_{GS} = 10V, R_G = 6\Omega$                |  |
| Turn-Off Fall Time                                    | t <sub>f</sub>       | -    | 13   | -    | ns   | ]  |  |

Notes: 7. Short duration pulse test used to minimize self-heating effect.







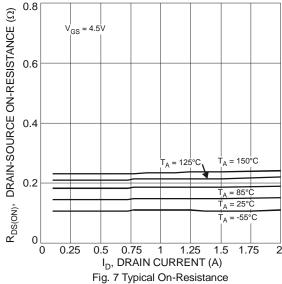
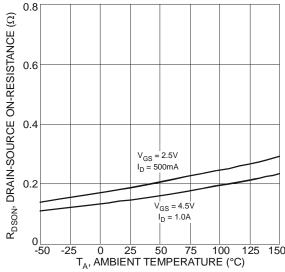


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature





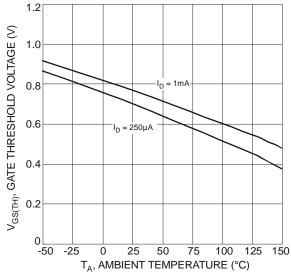
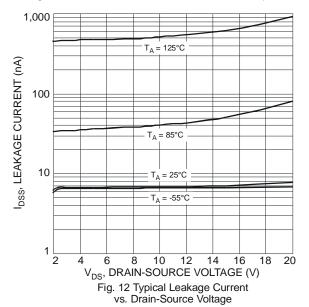
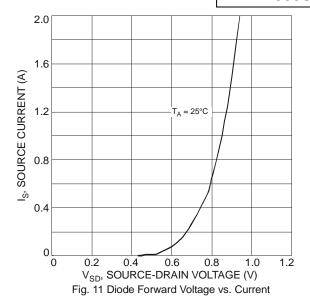


Fig. 10 Gate Threshold Variation vs. Ambient Temperature



8 V<sub>DS</sub> = 15V V<sub>DS</sub> = 15V V<sub>DS</sub> = 15V V<sub>DS</sub> = 1A V<sub>DS</sub> = 15V V<sub>DS</sub> = 15V



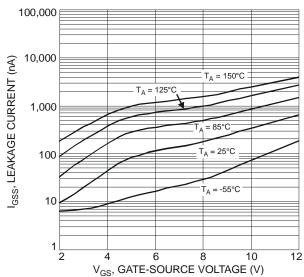
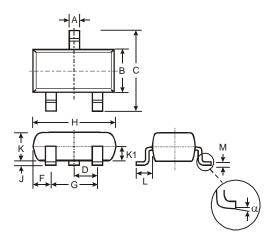


Fig.13 Leakage Current vs. Gate-Source Voltage

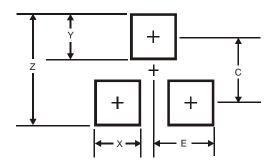


# **Package Outline Dimensions**



|     | SOT23                |      |       |  |  |  |  |
|-----|----------------------|------|-------|--|--|--|--|
| Dim | Min                  | Max  | Тур   |  |  |  |  |
| Α   | 0.37                 | 0.51 | 0.40  |  |  |  |  |
| В   | 1.20                 | 1.40 | 1.30  |  |  |  |  |
| С   | 2.30                 | 2.50 | 2.40  |  |  |  |  |
| D   | 0.89                 | 1.03 | 0.915 |  |  |  |  |
| F   | 0.45                 | 0.60 | 0.535 |  |  |  |  |
| G   | 1.78                 | 2.05 | 1.83  |  |  |  |  |
| Н   | 2.80                 | 3.00 | 2.90  |  |  |  |  |
| J   | 0.013                | 0.10 | 0.05  |  |  |  |  |
| K   | 0.903                | 1.10 | 1.00  |  |  |  |  |
| K1  | -                    | 1    | 0.400 |  |  |  |  |
| L   | 0.45                 | 0.61 | 0.55  |  |  |  |  |
| M   | 0.085                | 0.18 | 0.11  |  |  |  |  |
| α   | 0°                   | 8°   | -     |  |  |  |  |
| All | All Dimensions in mm |      |       |  |  |  |  |

# **Suggested Pad Layout**



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.9           |
| Х          | 0.8           |
| Y          | 0.9           |
| С          | 2.0           |
| E          | 1.35          |





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